

## ABSTRACT OF THE DISCLOSURE

A first on-wafer intended pattern and first and second on-wafer alignment marks have been formed in a reference layer that has been formed on a wafer by using a reference-  
5 layer-defining photomask. The first on-wafer intended pattern is a part of an isolation film pattern. The first on-wafer alignment mark has the same width and space as those of the first on-wafer intended pattern. The second on-wafer alignment mark has the same width and space as those of a  
10 second intended pattern for a layer-to-be-aligned to be formed on the reference layer. A shift  $\Delta x$  is caused between the first and second on-wafer alignment marks because the diffraction of light affects rough and fine patterns on the photomask differently. In performing alignment by reference  
15 to the first alignment mark, the position of a mask to be aligned is corrected by the shift  $\Delta x$ .